

Remarks

Reconsideration of this Application is respectfully requested.

Upon entry of the foregoing amendment, claims 13, 14, 16, 18, 20, 21 and 53 are pending in the application, with claim 13 being the independent claim.

The first page of the specification has been amended to more accurately reflect the priority claim made in the present application. This change is believed to introduce no new matter, and its entry is respectfully requested.

Based on the above amendment and the following remarks, Applicant respectfully requests that the Examiner reconsider all outstanding objections and rejections and that they be withdrawn.

Information Disclosure Statements

In the pending Office Action, the Examiner indicated that the Information Disclosure Statements filed by Applicant on June 27, 2000, August 28, 2002 and October 15, 2002 were not accompanied by associated Forms PTO-1449. However, Applicant's records show that each of these Information Disclosure Statements was filed with a corresponding Form PTO-1449. Moreover, Examiner James Davie provided acknowledged copies of these Forms PTO-1449 to Applicant along with a Notice of Allowance issued in the present application on May 5, 2003 (a copy of the Notice of Allowance with acknowledged Forms PTO-1449 is provided herewith). The acknowledged Forms PTO-1449 show that Examiner Davie reviewed and signed off on each of the references cited in these Information Disclosure Statements. Accordingly, it

is respectfully submitted that Applicant should not be required to resubmit the Information Disclosure Statements already filed on June 27, 2000, August 28, 2002 and October 15, 2002.

Certified Copies of Foreign Applications upon which Priority Claim is Based

In the pending Office Action, the Examiner acknowledged Applicant's claim for foreign priority but requested that Applicant file a certified copy of the foreign applications as required by 35 U.S.C. § 119(b). However, in the filing papers filed in the present application on June 27, 2000, Applicant stated that certified copies of the priority applications were filed on September 14, 1995 in prior Application No. 08/528,308 and that the filing of the certified copies was acknowledged in an Office Action dated June 20, 1996. As set forth in M.P.E.P. § 201.14(b):

Where the benefit of a foreign filing date based on a foreign application is claimed in a later filed application (i.e., continuation, continuation-in-part, division) or in a reissue application and a certified copy of the foreign application as filed, has been filed in a parent or related application, it is not necessary to file an additional certified copy in the later application. A reminder of this provision is found in form paragraph 2.20. ***The applicant when making such claim for priority may simply identify the application containing the certified copy.*** In such cases, the examiner should acknowledge the claim on form PTOL-326.

(Emphasis added). Since Applicant has already identified the application containing the certified copies in accordance with this rule, it is respectfully submitted that Applicant should not be required to provide additional certified copies of these foreign applications.

Obviousness-Type Double Patenting Rejections

The Examiner has provisionally rejected claims 13, 14, 16, 18, 20, 21 and 53 under the judicially created doctrine of obviousness-type double patenting rejection as being unpatentable over claims 1-45 of priority U.S. Patent No. 6,084,899 to Shakuda and claims 1-23 of priority U.S. Patent No. 6,115,399 to Shakuda. Applicant obviates these obviousness-type double patenting rejections based upon the terminal disclaimer submitted herewith. Accordingly, Applicant respectfully requests that these rejections be reconsidered and withdrawn.

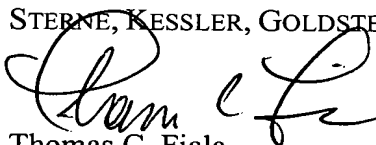
Conclusion

All of the stated grounds of objection and rejection have been properly traversed, accommodated, or rendered moot. Applicant therefore respectfully requests that the Examiner reconsider all presently outstanding objections and rejections and that they be withdrawn. Applicant believes that a full and complete reply has been made to the outstanding Office Action and, as such, the present application is in condition for allowance. If the Examiner believes, for any reason, that personal communication will expedite prosecution of this application, the Examiner is invited to telephone the undersigned at the number provided.

Prompt and favorable consideration of this Amendment and Reply is respectfully requested.

Respectfully submitted,

STERNE, KESSLER, GOLDSTEIN & FOX P.L.L.C.



Thomas C. Fiala
Attorney for Applicant
Registration No. 43,610

Date: 12/8/04

1100 New York Avenue, N.W.
Washington, D.C. 20005-3934
(202) 371-2600
329798v1

PART B - FEE(S) TRANSMITTAL

Complete and send this form, together with applicable fee(s), to: **Mail** Box ISSUE FEE
Commissioner for Patents
Alexandria, Virginia 22313-1450
Fax (703)746-4000

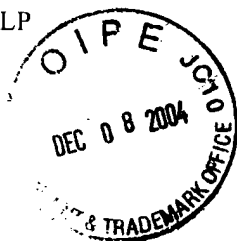
INSTRUCTIONS: This form should be used for transmitting the ISSUE FEE and PUBLICATION FEE (if required). Blocks 1 through 4 should be completed where appropriate. All further correspondence including the Patent, advance orders and notification of maintenance fees will be mailed to the current correspondence address as indicated unless corrected below or directed otherwise in Block 1, by (a) specifying a new correspondence address; and/or (b) indicating a separate "FEE ADDRESS" for maintenance fee notifications.

CURRENT CORRESPONDENCE ADDRESS (Note: Legibly mark-up with any corrections or use Block 1)

7590

05/05/2003

Burns Doane Swecker & Mathis LLP
 1737 King Street Suite 500
 Alexandria, VA 22314-2756



Note: A certificate of mailing can only be used for domestic mailings of the Fee(s) Transmittal. This certificate cannot be used for any other accompanying papers. Each additional paper, such as an assignment or formal drawing, must have its own certificate of mailing or transmission.

Certificate of Mailing or Transmission

I hereby certify that this Fee(s) Transmittal is being deposited with the United States Postal Service with sufficient postage for first class mail in an envelope addressed to the Box Issue Fee address above, or being facsimile transmitted to the USPTO, on the date indicated below.

(Depositor's name)
(Signature)
(Date)

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/604,097	06/27/2000	Yukio Shakuda	033022-004	6648

TITLE OF INVENTION: SEMICONDUCTOR LIGHT EMITTING DEVICE AND MANUFACTURING METHOD THEREFOR

APPLN. TYPE	SMALL ENTITY	ISSUE FEE	PUBLICATION FEE	TOTAL FEE(S) DUE	DATE DUE
nonprovisional	NO	\$1300	\$0	\$1300	08/05/2003

EXAMINER	ART UNIT	CLASS-SUBCLASS
DAVIE, JAMES W	2828	372-046000

1. Change of correspondence address or indication of "Fee Address" (37 CFR 1.363).

- ☐ Change of correspondence address (or Change of Correspondence Address form PTO/SB/122) attached.
- ☐ "Fee Address" indication (or "Fee Address" Indication form PTO/SB/47; Rev. 03-02 or more recent) attached. Use of a **Customer Number is required.**

2. For printing on the patent front page, list (1) the names of up to 3 registered patent attorneys or agents OR, alternatively, (2) the name of a single firm (having as a member a registered attorney or agent) and the names of up to 2 registered patent attorneys or agents. If no name is listed, no name will be printed.

1 _____

2 _____

3 _____

3. ASSIGNEE NAME AND RESIDENCE DATA TO BE PRINTED ON THE PATENT (print or type)

PLEASE NOTE: Unless an assignee is identified below, no assignee data will appear on the patent. Inclusion of assignee data is only appropriate when an assignment has been previously submitted to the USPTO or is being submitted under separate cover. Completion of this form is NOT a substitute for filing an assignment.

(A) NAME OF ASSIGNEE

(B) RESIDENCE: (CITY and STATE OR COUNTRY)

Please check the appropriate assignee category or categories (will not be printed on the patent) ☐ individual ☐ corporation or other private group entity ☐ government

4a. The following fee(s) are enclosed:

- ☐ Issue Fee
- ☐ Publication Fee
- ☐ Advance Order - # of Copies _____

4b. Payment of Fee(s):

- ☐ A check in the amount of the fee(s) is enclosed.
- ☐ Payment by credit card. Form PTO-2038 is attached.
- ☐ The Commissioner is hereby authorized by charge the required fee(s), or credit any overpayment, to Deposit Account Number _____ (enclose an extra copy of this form).

Commissioner for Patents is requested to apply the Issue Fee and Publication Fee (if any) or to re-apply any previously paid issue fee to the application identified above.

(Authorized Signature)

(Date)

NOTE: The Issue Fee and Publication Fee (if required) will not be accepted from anyone other than the applicant; a registered attorney or agent; or the assignee or other party in interest as shown by the records of the United States Patent and Trademark Office.

This collection of information is required by 37 CFR 1.311. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Alexandria, Virginia 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Alexandria, Virginia 22313-1450.

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TRANSMIT THIS FORM WITH FEE(S)



UNITED STATES PATENT AND TRADEMARK OFFICE

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United States Patent and Trademark Office
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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/604,097	06/27/2000	Yukio Shakuda	033022-004	6648

7590 05/05/2003

Burns Doane Swecker & Mathis LLP
1737 King Street Suite 500
Alexandria, VA 22314-2756
UNITED STATES

EXAMINER

DAVIE, JAMES W

ART UNIT

PAPER NUMBER

2828

DATE MAILED: 05/05/2003

Notice of Fee Increase on January 1, 2003

If a reply to a "Notice of Allowance and Fee(s) Due" is filed in the Office on or after January 1, 2003, then the amount due will be higher than that set forth in the "Notice of Allowance and Fee(s) Due" since there will be an increase in fees effective on January 1, 2003. See Revision of Patent and Trademark Fees for Fiscal Year 2003; Final Rule, 67 Fed. Reg. 70847, 70849 (November 27, 2002).

The current fee schedule is accessible from: <http://www.uspto.gov/main/howtofees.htm>.

If the issue fee paid is the amount shown on the "Notice of Allowance and Fee(s) Due," but not the correct amount in view of the fee increase, a "Notice to Pay Balance of Issue Fee" will be mailed to applicant. In order to avoid processing delays associated with mailing of a "Notice to Pay Balance of Issue Fee," if the response to the Notice of Allowance and Fee(s) due form is to be filed on or after January 1, 2003 (or mailed with a certificate of mailing on or after January 1, 2003), the issue fee paid should be the fee that is required at the time the fee is paid. If the issue fee was previously paid, and the response to the "Notice of Allowance and Fee(s) Due" includes a request to apply a previously-paid issue fee to the issue fee now due, then the difference between the issue fee amount at the time the response is filed and the previously paid issue fee should be paid. See Manual of Patent Examining Procedure, Section 1308.01 (Eighth Edition, August 2001).

Questions relating to issue and publication fee payments should be directed to the Customer Service Center of the Office of Patent Publication at (703) 305-8283.



UNITED STATES PATENT AND TRADEMARK OFFICE

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www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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09/604,097

06/27/2000

Yukio Shakuda

033022-004

6648

7590

05/05/2003

EXAMINER

DAVIE, JAMES W

Burns Doane Swecker & Mathis LLP
1737 King Street Suite 500
Alexandria, VA 22314-2756

ART UNIT

PAPER NUMBER

2828

DATE MAILED: 05/05/2003

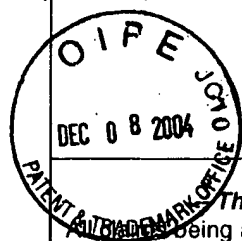
Determination of Patent Term Adjustment under 35 U.S.C. 154 (b) (application filed on or after May 29, 2000)

The patent term adjustment to date is 234 days. If the issue fee is paid on the date that is three months after the mailing date of this notice and the patent issues on the Tuesday before the date that is 28 weeks (six and a half months) after the mailing date of this notice, the term adjustment will be 234 days.

If a continued prosecution application (CPA) was filed in the above-identified application, the filing date that determines patent term adjustment is the filing date of the most recent CPA.

Applicant will be able to obtain more detailed information by accessing the Patent Application Information Retrieval (PAIR) system. (<http://pair.uspto.gov>)

Any questions regarding the patent term extension or adjustment determination should be directed to the Office of Patent Legal Administration at (703)305-1383.



Notice of Allowability

Application No.

09/604,097

Applicant(s)

SHAKUDA, YUKIO

Examiner

James W Davie

Art Unit

2828

The MAILING DATE of this communication appears on the cover sheet with the correspondence address— being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. ☒ This communication is responsive to amendment filed 4/14/03.
2. ☒ The allowed claim(s) is/are 13-21.
3. ☒ The drawings filed on 27 June 2000 are accepted by the Examiner.
4. ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) ☐ All b) ☐ Some* c) ☐ None of the:
 1. ☐ Certified copies of the priority documents have been received.
 2. ☒ Certified copies of the priority documents have been received in Application No. 08/528,308.
 3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).
 - * Certified copies not received: _____.
5. ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
 - (a) ☐ The translation of the foreign language provisional application has been received.
6. ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. **THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.**

7. ☐ A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
8. ☐ CORRECTED DRAWINGS must be submitted.
 - (a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 - 1) ☐ hereto or 2) ☐ to Paper No. _____.
 - (b) ☐ including changes required by the proposed drawing correction filed _____, which has been approved by the Examiner.
 - (c) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No. _____.

Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the top margin (not the back) of each sheet. The drawings should be filed as a separate paper with a transmittal letter addressed to the Official Draftsperson.

9. ☐ DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

- | | |
|--|--|
| 1 <input type="checkbox"/> Notice of References Cited (PTO-892) | 2 <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3 <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 4 <input type="checkbox"/> Interview Summary (PTO-413), Paper No. _____ |
| 5 <input checked="" type="checkbox"/> Information Disclosure Statements (PTO-1449), Paper No. _____ | 6 <input checked="" type="checkbox"/> Examiner's Amendment/Comment |
| 7 <input type="checkbox"/> Examiner's Comment Regarding Requirement for Deposit of Biological Material | 8 <input type="checkbox"/> Examiner's Statement of Reasons for Allowance |
| | 9 <input type="checkbox"/> Other |

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

This application is in condition for allowance except for the presence of claims 22-52 to a Species non-elected without traverse. Accordingly, claims 22-52 have been cancelled.

Allowable Subject Matter

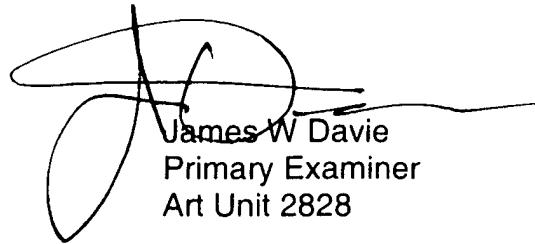
2. Claims 13-21 are allowed.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to James W Davie whose telephone number is (703) 308-4847. The examiner can normally be reached on M-F 9-5:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Paul Ip can be reached on (703) 308-3098. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7724 for regular communications and (703) 308-7724 for After Final communications.

Art Unit: 2828

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.



James W Davie
Primary Examiner
Art Unit 2828

jd
May 1, 2003

INFORMATION DISCLOSURE CITATION

PTO-1449

ATTORNEY'S DKT NO.
033022-004DIVISIONAL APPLICATION
OF NO. ~~09/012,790~~APPLICANT
Yukio SHAKUDAFILING DATE
June 27, 2000GROUP
2874 (expected)

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
JD	4,890,293	12/26/89	TANEYA et al.	372	46	
JD	5,218,613	06/08/93	SERREZE	372	45	
JD	4,567,060	01/28/86	HAYAKAWA et al.	488	44	
JD	5,210,767	05/11/93	ARIMOTO et al.	372	46	
JD	4,347,611	08/1982	SCIFRES et al.	372	45	
JD	4,982,409	01/1991	KINOSHITA et al.	372	45	
JD	5,592,502	07/07/97	MATSUMOTO et al.	372	45	
JD	5,619,518	04/08/97	HORIE et al.	372	45	
JD	5,578,839	11/26/96	NAKAMURA et al.	257	96	
JD	5,247,533	09/1993	OKAZAKI et al.	372	45	
JD	5,751,752	05/1998	SHAKUDA	372	45	

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
JD	477013A2	03/25/92	EUROPE				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

JD	Abstract of Japanese Patent Publication No. 02-129915, dated May 7, 1992, TSUNODA
JD	Strite et al., "Progress and Prospects for GaN and the III-V Nitride Semiconductors", THIN SOLID FILMS, Vol. 231, pp. 197-210 (no month available)
JD	Nakamura et al., "Candela-Class High-Brightness InGaN/AlGaIn Double-Heterostructure Blue-Light-Emitting Diodes"; APPLIED PHYSICS LETTERS, Vol. 64, No. 13, pp. 1687-1689
JD	Analysis Report No. 602020, dated April 25, 1994
JD	Unpublished Analysis Report (translation); Surface Analysis Second Group No. 602020
JD	Japanese Journal of Applied Physics, Vol. 32, No. 1A/B, dated January 15, 1993
JD	Applied Physics Letters, Vol. 64, No. 13, dated March 28, 1994
JD	IEEE Journal of Quantum Electronics, Vol. QE-17, No. 9, dated September 1981
JD	(3) Nitride Mixed Crystal (3 pages) - written agreement against Office Action for Japanese Application 06-219892 on which this application is based
JD	Isamu Akasaki, Advanced Electronics I-1, III-V, Group of Semiconductor Compound (1994); 1st Edition, Baifu-kan, p. 345-347

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Substitute for form 1449A/PTO

ATTORNEY'S DKT.
033022-004

APPLICATION No.
09/604,097

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

APPLICANT
Yukio SHAKUDA

FILING DATE
June 27, 2000

GROUP
6648

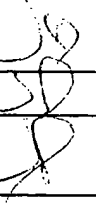

U.S. PATENT DOCUMENTS

[illegible]

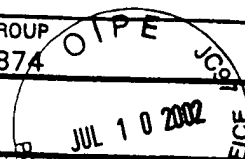
FOREIGN PATENT DOCUMENTS

Examiner Initials	Foreign Patent Document		Country	Date of Publication (MM-DD-YYYY)	Translation	
	Number	Kind Code (if known)			Yes	no
JD	6-268259		Japan	09-22-1994	X	
JD	7-312445		Japan	11-28-1995	X	
LD	2-229475		Japan	09-12-1990	X	

NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
	Blue Device Development Story (P1-6 and P10, ELECTRONICS, April 1999 issue) (with English Translation)		
	Semiconductor Laser (issued on October 25, 1994), (P44-P45) (with English Translation)		
	Device Physical Properties and Applications (P124-P125, The Fascination of Blue Light Emitting Device, issued on April 14, 1997) (with English Translation)		
Examiner Signature		Date Considered	10/24/02

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTORNEY'S FIRM NO.
033022-1APPLICATION NO.
09/604,097APPLICANT
Yukio ShakudaFILING DATE
June 27, 2000GROUP
2874

U.S. PATENT DOCUMENTS

Examiner Initials	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication (MM-DD-YYYY)
	Number	Kind Code (if known)		
JD	4,268,842		Jacob et al.	05/19/1981
JD	5,006,908		Matsuoka et al.	04/09/1991
JD	5,227,328		Khan et al.	07/13/1993
JD	4,144,116		Jacob et al.	03/13/1979
JD	5,252,499		Rothschild	10/12/1993
JD	4,904,618		Neumark	02/27/1990

FOREIGN PATENT DOCUMENTS

Examiner Initials	Foreign Patent Document		Country	Date of Publication (MM-DD-YYYY)	Translation	
	Number	Kind Code (if known)			Yes	no
JD	0 483 688 A2		Europe	05/06/1992		
JD	0 541 373 B1		Europe	09/30/1998		
JD	WO 96/11498		WIPO	04/18/1996		

NON-PATENT LITERATURE DOCUMENTS

Examiner Initials	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
JD	NAKAMURA et al., "Thermal Annealing Effect of P-Type Mg-Doped GaN Films", Jpn. J. Appl. Phys. Vol. 31 (1992), pp. L139-L142 Feb.
JD	WATANABE et al., "Annealing effect on the electrical properties of heavily C-doped p GaAs", Appl. Phys. Lett. 59 (4), July 22, 1991, American Institute of Physics
JD	Delphion, Intellectual Property Network, translation of U.S. 4,960,720, 2/18/01
JD	AMANO et al., "Electron Beam Effects on Blue Luminescence of Zinc-Doped GaN", Journal of Luminescence 40 & 41 (1998), pp. 121-122, Elsevier Science Publishers B.V., North-Holland, Amsterdam (No month)
JD	MARUSKA et al., "The Preparation and Properties of Vapo-Deposited Single-Crystal Line GaN", Applied Physics Letters, Vol. 15, No. 10, November 15, 1969
JD	JOHNSON et al., "Hydrogen passivation of shallow-acceptor impurities in p-type GaAs", Physical Review B, Vol. 33, No. 2, January 15, 1986, The American Physical Society
JD	ANTELL et al., "Passivation of zinc acceptors in InP by atomic hydrogen coming from arsine during metalorganic vapor phase epitaxy", 1988 (No month)
JD	AKASAKI et al., "Photoluminescence of Mg-doped p-type GaN and electroluminescence of GaN p-n junction LED", Journal of Luminescence 48 & 49, pp. 666-670, Elsevier Science Publishers B.V., North-Holland, 1991 (No month)
JD	KHAN et al., "P-type Conversion of Nitrogen Doped ZnSe Films Grown by MOCVD", pp. 251-256, Mat. Res. Soc. Symp. Proc. Vol. 222, 1991, Materials Research Society (No month)
JD	LAKS et al., "Native defects and self-compensation in ZnSe", pp. 10 965 - 10 978, Vol. 45, No. 19, Physical Review B, Vol. 45, No. 19, May 15, 1992, The American Physical Society
JD	VAN DE WALLE et al., "Solubilities defect reactions and doping limits in ZnSe", pp. 704-709, Journal of Crystal Growth 117, 1992, Elsevier Science Publishers B.V., North Holland (No month)
JD	LAKS et al., "Role of Native Defects in Wide-Band Gap Semiconductors", pp. 648-651, Physical Review Letters, Vol. 66, No. 5, 1991, The American Physical Society
JD	NEUMARK et al., "Li Doped ZnSe and Problems of p-Type Conduction", pp. 189-194, Journal of Crystal Growth 59, 1982, North Holland Publishing Company (No month)
Examiner Signature	Date Considered
James P. ...	10/22/02

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

APPLICANT

Yukio Shakuda

FILING DATE

June 27, 2000

GROUP/TYPE

2874

O I P E J C 97
DEC 08 2004
PATENT & TRADEMARK

PATE JUL 10 2002
J C 97
TRADEMARK

U.S. PATENT DOCUMENTS

Examiner Initials	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication (MM-DD-YYYY)
	Number	Kind Code (If known)		
JSD	6,084,899		Shakuda	07/04/2000
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Examiner Initials	Foreign Patent Document		Country	Date of Publication (MM-DD-YYYY)	Translation	
	Number	Kind Code (If known)			Yes	no

NONPATENT LITERATURE DOCUMENTS

Examiner Initials	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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Examiner Signature	<i>James Doe</i>	Date Considered	10/22/02
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTORNEY'S FIRM NO.

033022-6

APPLICATION NO.

09/604,097

APPLICANT

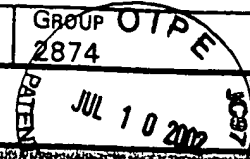
Yukio Shakuda

FILING DATE

June 27, 2000

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Examiner Initials	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication (MM-DD-YYYY)
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NON-PATENT LITERATURE DOCUMENTS

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JD	Response letter to Oppositions by A.A. Thornton & Co., dated March 3, 2000

Examiner Signature	Date Considered
<i>[Signature]</i>	10/22/02

EXAMINER: Initial reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

No.

APPLICATION NO.
09/604,097

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

APPLICANT
Yukio SHAKUDA

FILING DATE
June 27, 2000

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2828

U.S. PATENT DOCUMENTS

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NON PATENT LITERATURE DOCUMENTS

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<i>[Signature]</i>	10/23/02

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.